

### PDFN56



Pin Definition:1. Source8. Drain2. Source7. Drain3. Source6. Drain4. Gate5. Drain

### **Key Parameter Performance**

Parameter	Value	Unit
V <sub>DS</sub>	100	V
R <sub>DS(on)</sub> (max)	12	mΩ
Qg	145	nC

#### **Block Diagram**

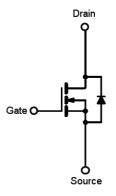
Features

- Low On-Resistance
- Low Input Capacitance
- Low Gate Charge

#### **Ordering Information**

Part No.	Package	Packing			
TSM120N10PQ56 RLG	PDFN56	2.5kpcs / 13" Reel			

**Note:** "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



N-Channel MOSFET

#### Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	100	V	
Gate-Source Voltage		V <sub>GS</sub>	±20	V	
Continuous Drain Current (Note 3)	T <sub>C</sub> =25°C		58	А	
	T <sub>A</sub> =25°C	- I <sub>D</sub>	16.1		
Drain Current-Pulsed (Note 1)		I <sub>DM</sub>	150	А	
Single Pulse Avalanche Energy L=0.5mH		E <sub>AS</sub>	156	mJ	
Maximum Power Dissipation (Note 2)	T <sub>C</sub> =25°C		36	W	
	T <sub>A</sub> =25°C	– P <sub>D</sub>	2		
Storage Temperature Range		T <sub>STG</sub>	-55 to +150	°C	
Operating Junction Temperature Range		TJ	-55 to +150	°C	

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	R <sub>eJC</sub>	1.2	°C/W
Thermal Resistance - Junction to Ambient	$R_{\Theta JA}$	62	°C/W



#### Electrical Specifications (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static				•		
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	100			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 30A$	R <sub>DS(ON)</sub>		10	12	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	V <sub>GS(TH)</sub>	2	3	4	V
Zero Gate Voltage Drain Current	$V_{DS} = 80V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μA
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Dynamic					•	
Total Gate Charge	$V_{DS} = 50V, I_D = 30A,$	Qg		145		nC
Gate-Source Charge		Q <sub>gs</sub>		25		
Gate-Drain Charge	V <sub>GS</sub> = 10V	$Q_{gd}$		43		
Input Capacitance	$V_{DS} = 30V, V_{GS} = 0V,$ f = 1.0MHz	C <sub>iss</sub>		3902		
Output Capacitance		C <sub>oss</sub>		251		pF
Reverse Transfer Capacitance		C <sub>rss</sub>		93		1
Switching					•	
Turn-On Delay Time		t <sub>d(on)</sub>		27		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 50V,$	t <sub>r</sub>		13		
Turn-Off Delay Time	$R_{\rm G} = 3\Omega, I_{\rm D} = 30A$	t <sub>d(off)</sub>		15		ns
Turn-Off Fall Time		t <sub>f</sub>		42		
Drain-Source Diode Characteristic	s and Maximum Rating	•		•		
Drain-Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =30A	$V_{SD}$			1.3	V
Reverse Recovery Time		t <sub>rr</sub>		65		ns
Reverse Recovery Charge	I <sub>S</sub> = 30A, dl/dt = 100A/μs	Q <sub>rr</sub>		175		nC

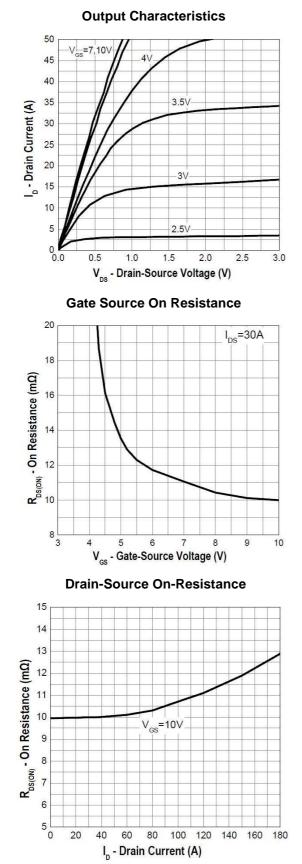
1. Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

2.  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.  $R_{\Theta JA}$  shown below for single device operation on FR-4 PCB in still air

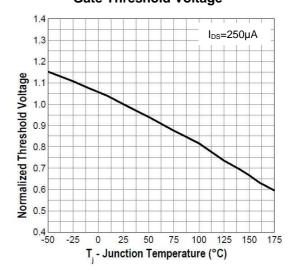
3. The maximum current is limited by package.



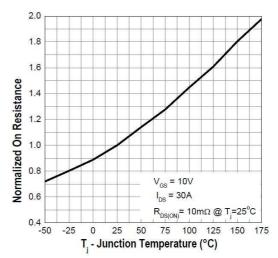
#### **Electrical Characteristics Curves**



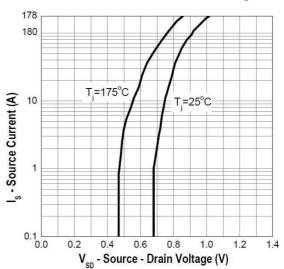
Gate Threshold Voltage



**Drain-Source On Resistance** 

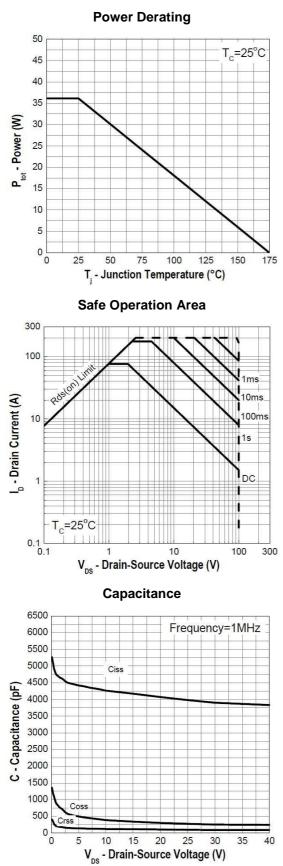


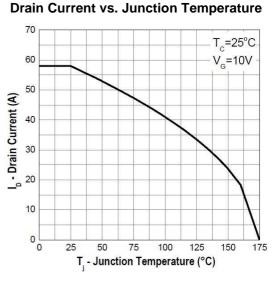
Source-Drain Diode Forward Voltage



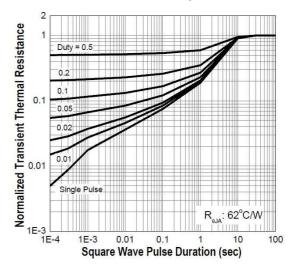


#### **Electrical Characteristics Curves**

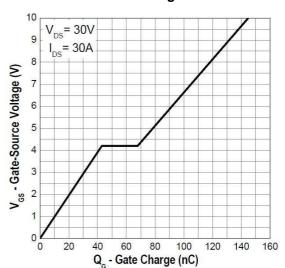




**Transient Thermal Impedance** 

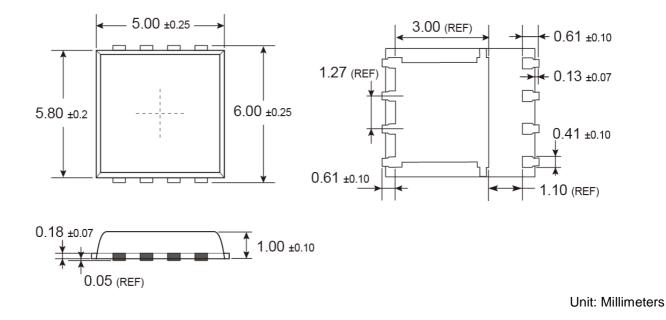


**Gate Charge** 





# **PDFN56 Mechanical Drawing**



### **Marking Diagram**



- Y = Year Code
- M = Month Code for Halogen Free Product
  (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)
- L = Lot Code



### Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.

## **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Taiwan Semiconductor manufacturer:

Other Similar products are found below :

614233C 648584F MCH3443-TL-E MCH6422-TL-E FDPF9N50NZ FW216A-TL-2W FW231A-TL-E APT5010JVR NTNS3A92PZT5G IRF100S201 JANTX2N5237 2SK2464-TL-E 2SK3818-DL-E FCA20N60\_F109 FDZ595PZ STD6600NT4G FSS804-TL-E 2SJ277-DL-E 2SK1691-DL-E 2SK2545(Q,T) D2294UK 405094E 423220D MCH6646-TL-E TPCC8103,L1Q(CM 367-8430-0972-503 VN1206L 424134F 026935X 051075F SBVS138LT1G 614234A 715780A NTNS3166NZT5G 751625C 873612G IRF7380TRHR IPS70R2K0CEAKMA1 RJK60S3DPP-E0#T2 RJK60S5DPK-M0#T0 APT5010JVFR APT12031JFLL APT12040JVR DMN3404LQ-7 NTE6400 JANTX2N6796U JANTX2N6784U JANTXV2N5416U4 SQM110N05-06L-GE3 SIHF35N60E-GE3